



UTG25N65-S

Preliminary

Insulated Gate Bipolar Transistor

**650V TRENCH GATE
FIELD-STOP IGBT**

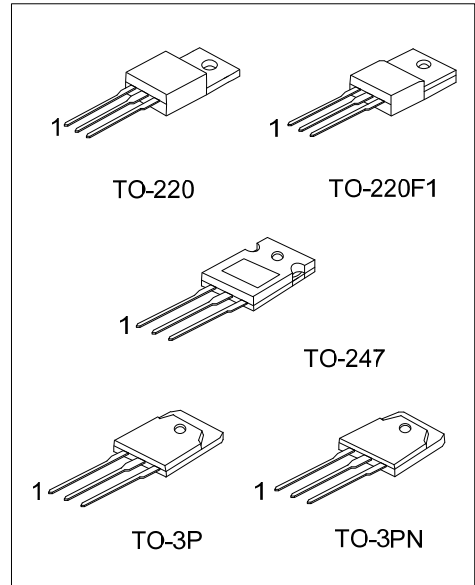
■ DESCRIPTION

The UTC **UTG25N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

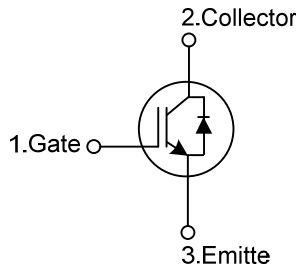
The UTC **UTG25N65-S** is suitable for the resonant or soft switching applications.

■ FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT),Typ.}=1.65V @ I_C=25A, V_{GE}=15V$
($T_C = 25^{\circ}C$)



■ SYMBOL



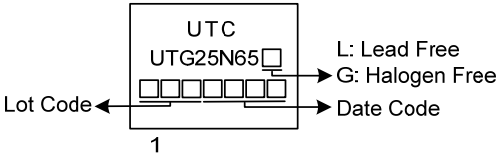
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTG25N65L-TA3-T	UTG25N65G-TA3-T	TO-220	G	C	E	Tube
UTG25N65L-TF1-T	UTG25N65G-TF1-T	TO-220F1	G	C	E	Tube
UTG25N65L-T47-T	UTG25N65G-T47-T	TO-247	G	C	E	Tube
UTG25N65L-T3P-T	UTG25N65G-T3P-T	TO-3P	G	C	E	Tube
UTG25N65L-T3N-T	UTG25N65G-T3N-T	TO-3PN	G	C	E	Tube

Note: Pin Assignment: G: Gate C: Collector E: Emitter

<p>UTG25N65G-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF1: TO-220F1, T47: TO-247, T3P: TO-3P, T3N: TO-3PN</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V_{CES}	650	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Transient Gate-emitter voltage ($t_p < 5$ ms)			± 25	V
Continuous Collector Current	$T_C=25^\circ\text{C}$	I_C	50	A
	$T_C=100^\circ\text{C}$		25	A
Collector Current Pulsed (Note 1)		I_{CM}	100	A
Diode Forward Current	$T_C=25^\circ\text{C}$	I_F	50	A
	$T_C=100^\circ\text{C}$		25	A
Short Circuit Withstand Time $V_{GE} = 15\text{V}$, $V_{CC} \leq 200\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{VJ} = 25^\circ\text{C}$		t_{SC}	3	μs
Power Dissipation ($T_C=25^\circ\text{C}$)	TO-220	P_D	100	W
	TO-220F1		35	W
	TO-247		290	W
	TO-3P/TO-3PN		313	W
Operating Junction Temperature		T_J	-40 ~ +175	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +175	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

2. Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Case	TO-220	θ_{JC}	1.25	$^\circ\text{C/W}$
	TO-220F1		3.57	$^\circ\text{C/W}$
	TO-247		0.43	$^\circ\text{C/W}$
	TO-3P/TO-3PN		0.4	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Off Characteristics							
Collector-Emitter Breakdown Voltage	BV _{CES}		650			V	
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V			5	μA	
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V			±400	nA	
On Characteristics							
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}	4.5		6.5	V	
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =25A, V _{GE} =15V	T _C =25°C	1.65	2.1	V	
			T _C =125°C	2.0		V	
Dynamic Characteristics							
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz		1150		pF	
Output Capacitance	C _{OES}			96		pF	
Reverse Transfer Capacitance	C _{RES}			16.4		pF	
Switching Characteristics							
Total Gate Charge	Q _G	V _{CE} =520V, I _C =25A, V _{GE} =15V		63.9		nC	
Gate-Emitter Charge	Q _{GE}			22.4		nC	
Gate-Collector Charge	Q _{GC}			22.4		nC	
Turn-On Delay Time	t _{DON)}	V _{CC} =400V, I _C =25A, R _G =5Ω, V _{GE} =0~15V, L=1000uH		19.7		ns	
Rise Time	t _R			19.8		ns	
Turn-Off Delay Time	t _{DOFF)}			40.2		ns	
Fall Time	t _F			76.6		ns	
Turn-On Switching Loss	E _{ON}			0.4		mJ	
Turn-Off Switching Loss	E _{OFF}			0.66		mJ	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Forward Voltage Drop	V _F		I _F =25A			3.0	V
Reverse Recovery Time	t _{rr}	I _F =25A, di/dt=100A/μS, V _{CC} =400V		53		ns	
Reverse Recovery Charge	Q _{rr}			353		nC	

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